

CLAIM LISTING:

1. (Currently Amended) A method of fabricating a semiconductor device, comprising ~~the steps of~~:
forming a first insulation film on a substrate by a spin-on process;
applying a curing process to said first insulation film at a temperature of 380 - 500°C over a duration of 5 – 180 seconds; and
forming a second insulation film on said first insulation film by a spin-on process.
2. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said first insulation film comprises an organic material having a specific dielectric constant of 3.0 or less.
3. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said first insulation film comprises an organic material of aromatic group.
4. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said first insulation film is formed of a spin-on film selected from the group consisting of an SiNCH film, an SiOCH film, an organic SOG film, and an HSQ film.
5. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said second insulation film comprises an organic material having a specific dielectric constant of 3.0 or less.
6. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said second insulation film comprises an organic material of aromatic group.
7. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said second insulation film is formed of a spin-on film selected from the group consisting of an SiNCH film, an SiOCH film, an organic SOG film, and an HSQ film.
8. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said curing process is conducted at a temperature between 380 – 500°C over a duration of 10 – 150 seconds.

9. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said curing process is conducted at a temperature between 400 - 470°C over a duration of 10 – 150 seconds.

10. (Currently Amended) ~~A~~ The method as claimed in claim 1, wherein said curing process is conducted such that there is formed an intermixing layer between said first and second films.

11. (Currently Amended) A method of fabricating a semiconductor device, comprising ~~the steps of~~:

forming a first insulation film on a substrate by a spin-on process;
applying a curing process to said first insulation film at a temperature of 380 - 500°C over a duration of 5 – 180 seconds;

forming a second insulation film on said first insulation film by a spin-on process;
patterning said second insulation film to form an opening therein; and
etching said first insulation film while using said second insulation film as a mask.

12. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said first insulation film comprises an organic material having a specific dielectric constant of 3.0 or less.

13. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said first insulation film comprises an organic material of aromatic group.

14. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said first insulation film is formed of a spin-on film selected from the group consisting of an SiNCH film, an SiOCH film, an organic SOG film, and an HSQ film.

15. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said second insulation film comprises an organic material having a specific dielectric constant of 3.0 or less.

16. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said second insulation film comprises an organic material of aromatic group.

17. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said second insulation film is formed of a spin-on film selected from the group consisting of an SiNCH film, an SiOCH film, an organic SOG film, and an HSQ film.

18. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said curing process is conducted at a temperature between 380 – 500°C over a duration of 10 – 150 seconds.

19. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said curing process is conducted at a temperature between 400 - 470°C over a duration of 10 – 150 seconds.

20. (Currently Amended) ~~A~~ The method as claimed in claim 11, wherein said curing process is conducted such that there is formed an intermixing layer between said first and second films.